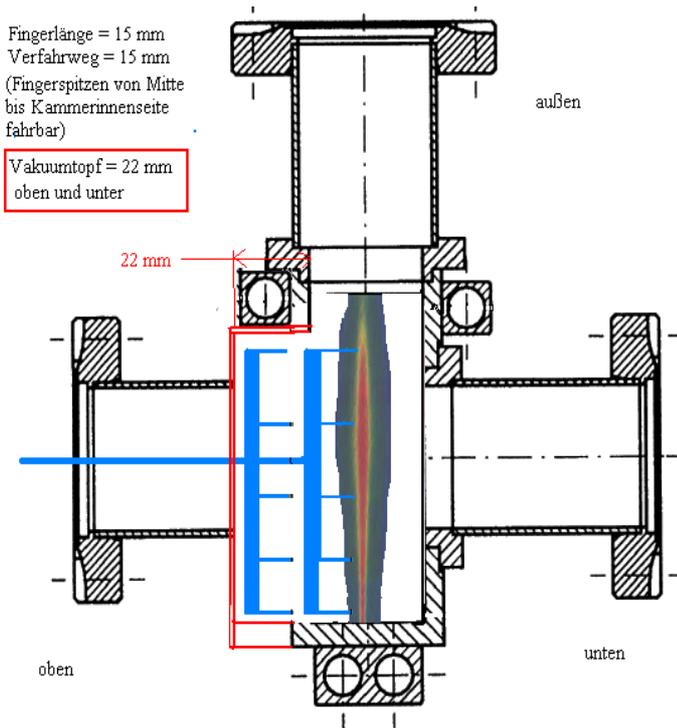


# Some thoughts concerning the SR- Monitor at 24 m for the LUMI upgrade

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## SR Monitor 24 m



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Fig. 1: Idea of the Monitor

All of the following calculations are done for a beam energy of 30 GeV and a current of 58 mA.

## Problem 1: Heat load of the Fingers:

- a: What is the energy-spectrum of the photons
- b: How many photons will hit the finger
- c: What is the energy deposition and the temperature increase
- d: cooling by radiation and secondaries and heat transport

### 1a) What is the energy-spectrum of the photons

Fig. 2 a, b shows that the critical energy  $E_c$  is widely spread between 10 and 200 keV.  $E_c$  is define by:  
 $E_c = \hbar \frac{2}{3} \gamma^3 \frac{c}{R}$ ,  $R$  = bending radius.

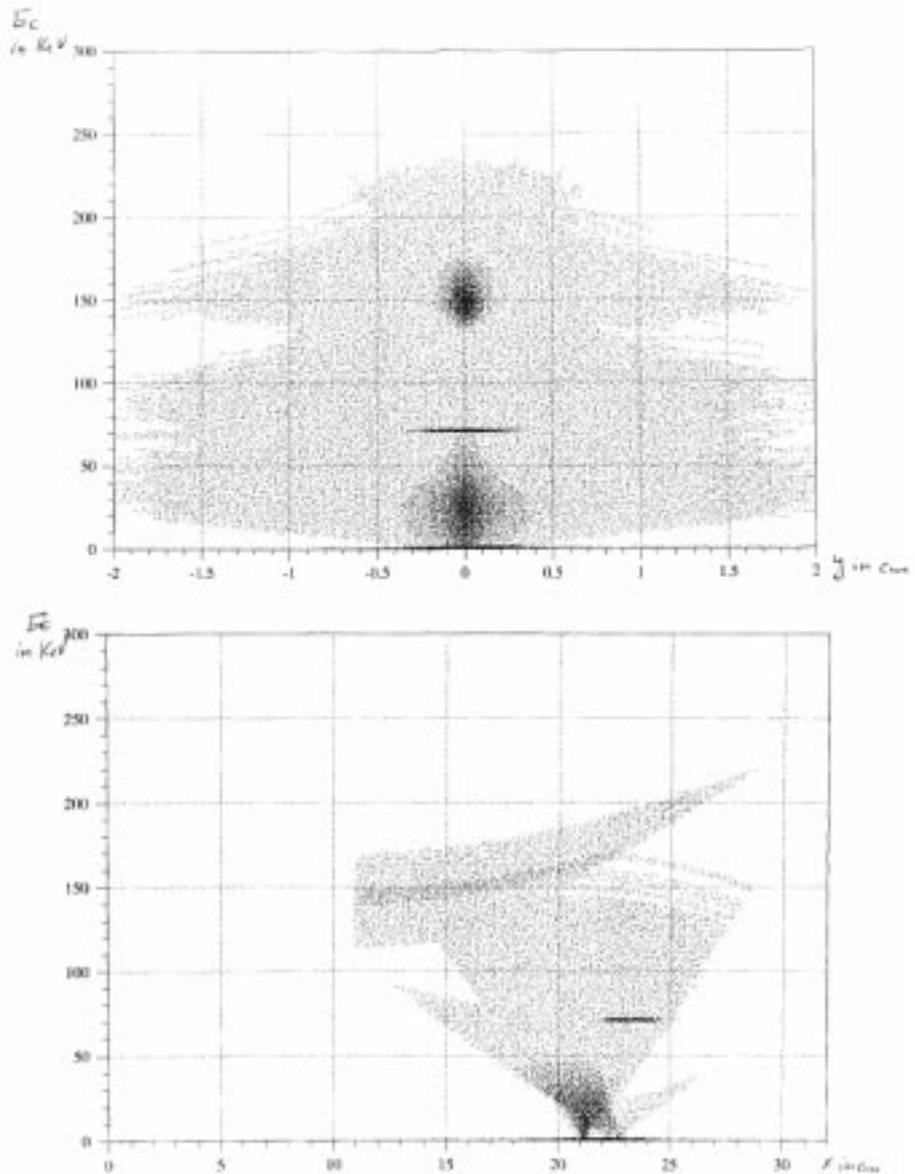


Fig. 2 a, b) Critical Energy  $E_c$  versus position at the SR-monitor ( $x$  = horizontal,  $y$  = vertical) by A. Mesek

The critical energy divides the power spectrum into two equal half's. Here the number of photons  $N$  is than derived from the total power by  $N/s = P/ E_c$ . Therefore for the heat load calculation one can use photons with  $E_\gamma = 100$  keV

**1b) How many photons will hit the finger**

We simulate a finger of 1 cm width in the SR-beam at  $x = 19-20$  cm and at  $y = -0.5 - 0.5$  cm. The amount of photons/s hitting the finger when driving in was calculated. The finger starts at  $y = 2$  cm and the other at  $x = 32$  cm, respectively. The integral number of photons from this point to the end of the finger at  $x'$  ( $y'$ ) is displayed in Fig. 4.

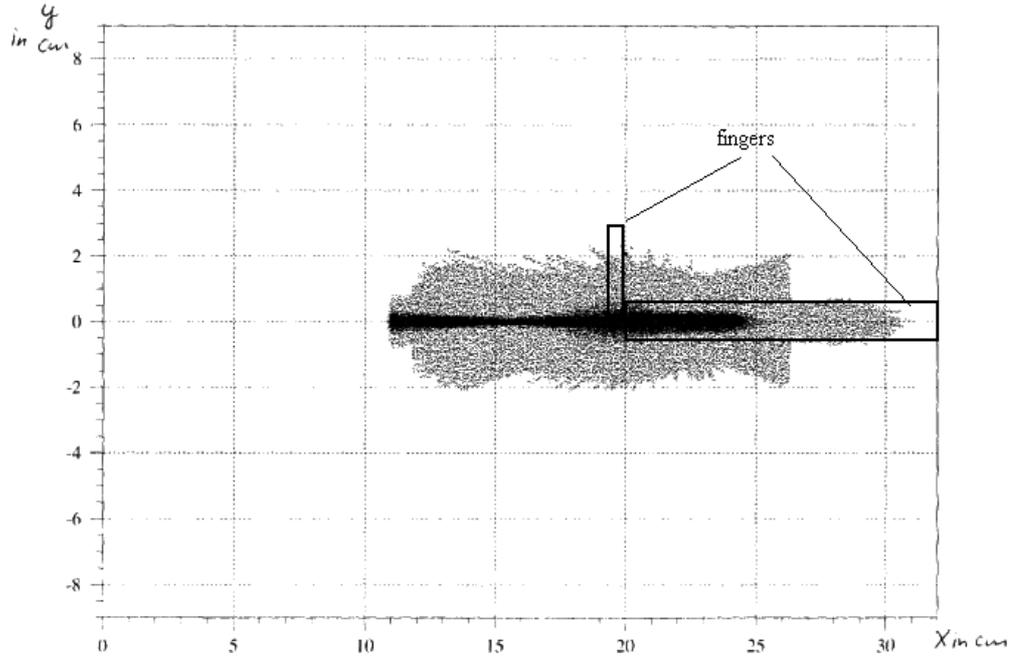


Fig 3: Photon distribution at the monitor with two fingers in measurement position; by A. Mesek

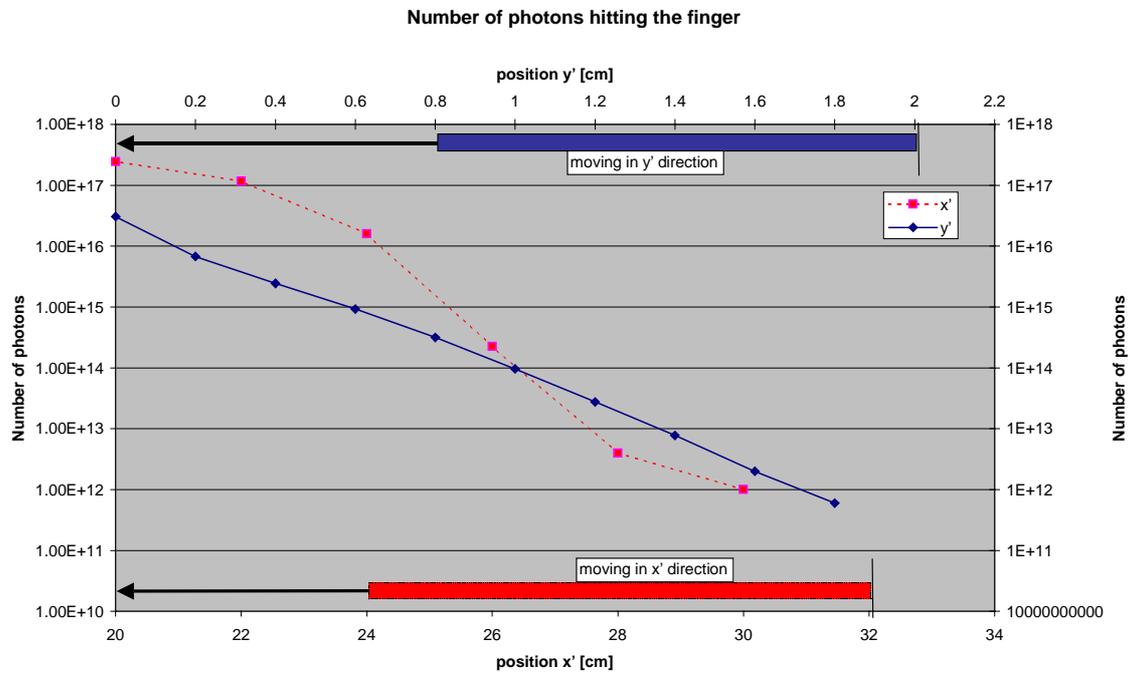


Fig. 4: Number of photons  $N_{x', y'}$ /s on the finger versus position of the finger

### **1c) What is the power deposition and the temperature increase**

Let us assume a Tungsten finger with a length of 3 cm (vertical) and 14 cm (horizontal) with a width of  $1.0 \cdot 1.0 \text{ cm}^2$ . A 100 keV Photon will be fully absorbed in 1 cm Tungsten. There is only a small amount <5% of backscattered photons. The deposited power can be calculated at any position of the finger by:

$$P = 100 \cdot 1000 \text{ eV} \cdot N_{x', y'/s} \cdot K \text{ [W]} \quad \text{with } K = 1.6 \cdot 10^{-19} \text{ eV/J}$$

If the finger reaches the middle of the SR one will have:

$$P(y' = 0) = 480 \text{ W}, \quad P(x' = 20) = 3920 \text{ W}$$

The temperature increase  $\Delta T$  can be calculated by:

$$\Delta T = P / (c_p \cdot G) \text{ with } G = \text{weight [g]} = V \rho, \rho = 19.39 \text{ g/cm}^3 \text{ and } c_p = \text{spec. heat cap.} = 0.134 \text{ J/(}^\circ\text{C g)}$$

$$\Delta T(y' = 0) = 46 \text{ }^\circ\text{C/s}; \quad \Delta T(x' = 20) = 107 \text{ }^\circ\text{C/s} \quad \text{with } V_{y'} = 4 \text{ cm}^3 \text{ and } V_{x'} = 14 \text{ cm}^3$$

In any case, this cannot be cooled down and has to be avoided! Maybe one can think about of three orders of magnitude less, because there will be no efficient cooling mechanism! Therefore  $y' = 1 \text{ cm}$  and  $x' = 26 \text{ cm}$ .

Other solutions:

- Water cooling of the fingers: no space
- Angle of  $30^\circ$  between SR and fingers: Factor 2 in length of finger gives factor 2 more material and therefore a reduction of factor 2 in temperature. Much smaller angles and therefore longer fingers do not fit into the monitor.
- Thinner fingers in SR direction: Reduction of  $N = N_0 \cdot \exp(-d \cdot \rho / \lambda)$  with  $d$  = thickness and  $\lambda$  = photon attenuation length  $\approx 0.5 \text{ g/cm}^2$  for 100 keV photons and W. Even with a 1mm thin tungsten finger (in SR direction) the absorption of the photons is still above 90 % (including backscattered photons). In this case the temperature is increased by the missing material by 1 order of magnitude. Much thinner fingers may help, but they do not have enough mechanical stability. And note also, that a huge number of photons with  $E_\gamma \ll E_c$  and therefore with a much smaller absorption length will hit the finger.
- Other thin materials: Much lighter materials with a high melting point will help: Carbon (diamond) and Beryllium. For C:  $\lambda = 5 \text{ g/cm}^2$ ,  $\rho = 2.2 \text{ g/cm}^3 \Rightarrow$  only 5% absorption; but  $(c_p \cdot G)_C / (c_p \cdot G)_W = 0.4 \Rightarrow$  Factor 2.5 more  $\Delta T$ . But expensive (diamond) and not easy to handle (Be). However, the cross section for the photo effect goes with  $Z^5$ , which is important for the signal yield (photocurrent).
- Thinner fingers transversal to SR direction: Assuming that (especially for the vertical finger) the distribution of the photons is homogeneous in the transversal plane,  $N$  is reduced by the width of the finger, but with the same amount the weight becomes reduced. Therefore no effect.
- Thin wires (Ref. 1) scanning the SR – beam: With this method, one will loose detailed information of the shape of the SR – beam. However, thin wires may be better cooled by radiation cooling and may be more rugged concerning the temperature issue.

**1d: Cooling by radiation and secondaries and heat transport**

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**2) Signal**

The signal comes from the emission of electrons due to the photoeffect. What is the efficiency of this process?

Some simplifications:

Let us assume that the radiation is a result of a simple bending magnet, so that

$$E_c = 100 \text{ keV. } \Rightarrow R = \hbar \frac{2}{3} \gamma^3 \frac{c}{E_c} = 266 \text{ m.}$$

According to [A3] in the appendix the total power/s is:

$$P_{\text{tot}} = \alpha \cdot W$$

while  $\alpha$  includes the geometry, the beam current and other approximations.

$$\text{Setting: } P_{\text{tot}} = P(x' = 26 \text{ cm}) \approx 4 \text{ W then } \alpha = P(x' = 26) / W = 4 \text{ W} / 7.7 \cdot 10^{-6} \text{ W} = 5.2 \cdot 10^5.$$

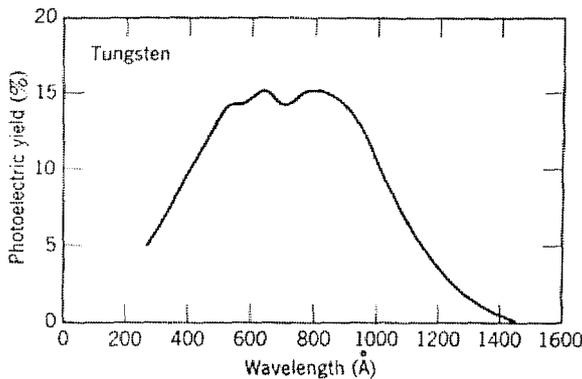
$$\text{and for y: } P_{\text{tot}} = P(y' = 1 \text{ cm}) \approx 0.4 \text{ W then } \alpha = P(x' = 1) / W = 0.4 \text{ W} / 7.7 \cdot 10^{-6} \text{ W} = 5.2 \cdot 10^4.$$

$\alpha$  is now the calibration constant which is true for power calculations within a certain photon energy ( $\hbar \omega$ ) range, especially for  $\omega \ll \omega_c$  which is the important range for calculating the photo current (see Fig. 5 and A2). Note that the opening angle  $\Theta$  of the SR for all photon energies will be neglected here because of the high  $\gamma$  ( $\Theta \sim 1/\gamma$ ). (is this also true for visible light?)

What is the interesting energy range for the photons producing photo current?

See Ref. 3! pages 224 – 244

For tungsten:



Photoelectric yields of W as a function of wavelength, normal incidence

Fig. 5, from Ref. 3

From Fig. 5: A Yield of approx. 10% / incident photon can be assumed over the wavelength between 200 to 1200 Å (20 – 120 nm)

$$\lambda_1 = 20 \text{ nm } \Rightarrow 2 \pi c / \lambda \text{ [1/s]} = 9.4 \cdot 10^{16} = \omega_1$$

$$\lambda_2 = 120 \text{ nm } \Rightarrow 2 \pi c / \lambda \text{ [1/s]} = 1.57 \cdot 10^{16} = \omega_2$$

Using Formula A1:

$$W = \alpha \cdot 0.52 \cdot \frac{e^2}{4 \pi \epsilon_0 R} \cdot \int_{\omega_1}^{\omega_2} \left( \frac{\omega R}{c} \right)^{1/3} d\omega = 6.5 \cdot 10^{-5} \text{ W for } x' = 26 \text{ cm}$$

Assuming a mean wavelength of  $\lambda = 70 \text{ nm} \Rightarrow$  One photon gives an Energy of  $E_\gamma = \hbar \omega = 2.8 \cdot 10^{-17} \text{ J}$ . To reach a Power of  $W$  one need  $N = W / E_\gamma = 2.3 \cdot 10^{12}$  Photons/s. With a photoelectric yield of 10% one will have  $2.3 \cdot 10^{11}$  Photoelectrons/s or a photocurrent of  $I_\gamma = 37 \text{ nA}$ .

This value should scale linear with the heat load (neglecting opening angle of SR). It agrees with experience from DORIS where at a total heat load of 27 W a Signal of in the order of some  $\mu\text{A}$  can be measured (Ref. 4). To measure the SR distribution (horizontal), the dynamic range of the electronic readout should cover at least 4 decades ( $1 \mu\text{A} - 0.1 \text{ nA}$ ). However, more will be better, but it should be extended to smaller currents. In this case we do not have to move each finger separately, because of the dynamic range of the readout and therefore in position (more than 1 cm vertical and more than 6 cm horizontal). Note that this result do not depend on the beam energy (as long as  $\omega \ll \omega_c$ ) but it depends on the beam current linear. This has to be taken into account when designing the dynamic range (about a factor 10)

Other Problems:

- 1) There is measured a cross talk of some ‰ between the fingers in DORIS (Ref. 4). Bias and shielding has to be designed carefully.
- 2) How the Power on the Finger will dissipate? This is the question of the insulation heating.
- 3) At high temperatures of the finger one will have thermal electrons emitted.

### **More important notes:**

From ref. 5 one can get some efficiency numbers for the x-ray photoeffect (at 9 keV). The efficiency is about 5%. that means, that there will be some big contributions to the calculated signal due to this effect. therefore the calculation gives more or less a lower limit!

Some Numbers: Let us assume a efficiency of 2% between 1 keV – 20 keV photon energy.

In this range one get  $1 \cdot 10^{14}$  Photons/s (10keV) or  $16 \mu\text{A}$ .

Maybe a filter which removes the Vacuum- ultraviolet may improve the monitor conditions because of reflections of low energy photons on the beam pipe walls?

AND: In case of this higher photon energy, one will have photoelectrons in the energy range of more than keV. Therefore a Bias of less than kV will not remove the cross talk between the fingers completely!!!!

## Appendix: Some curves

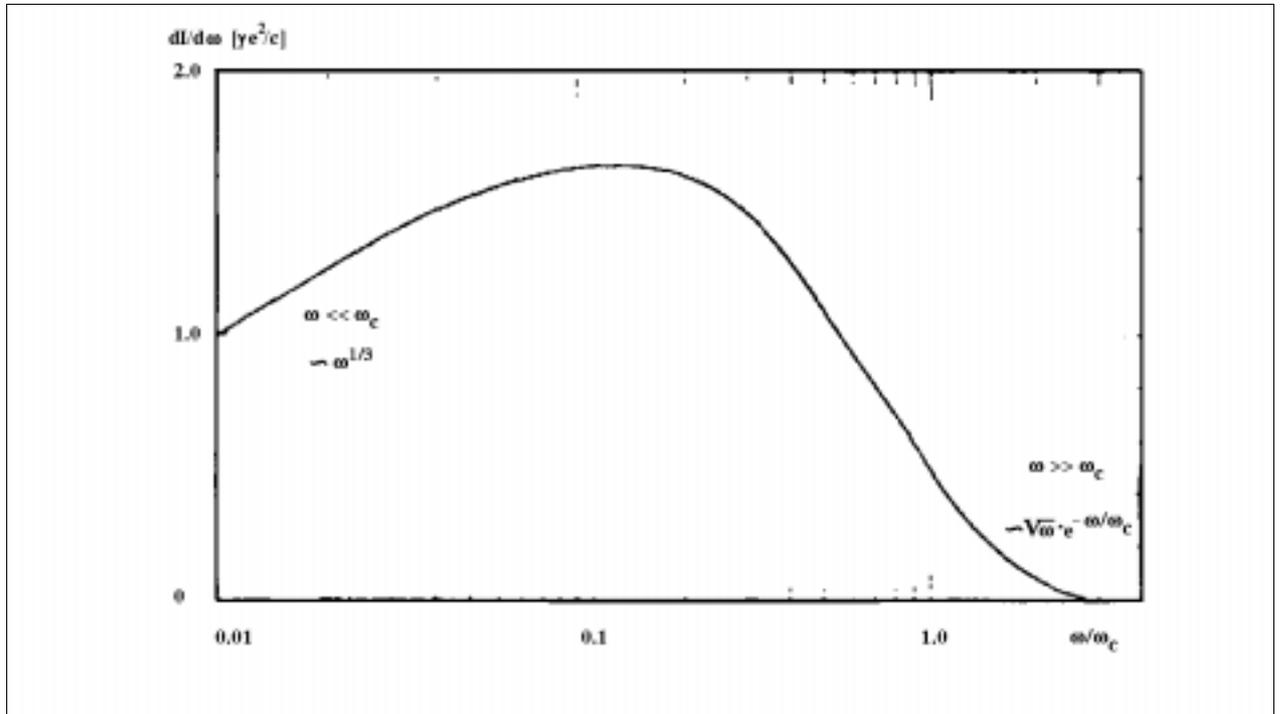


Fig. A1: Frequency - Spectrum of the Synchrotron Radiation.

Ref. 2 gives two approximations for the total radiated energy per turn electron and frequency interval  $d\omega$  of the photons (in MKSA units):

:

For  $\omega \ll \omega_c$  with  $\omega_c = E_c / \hbar$  (note that there is no dependence on the energy of the beam!):

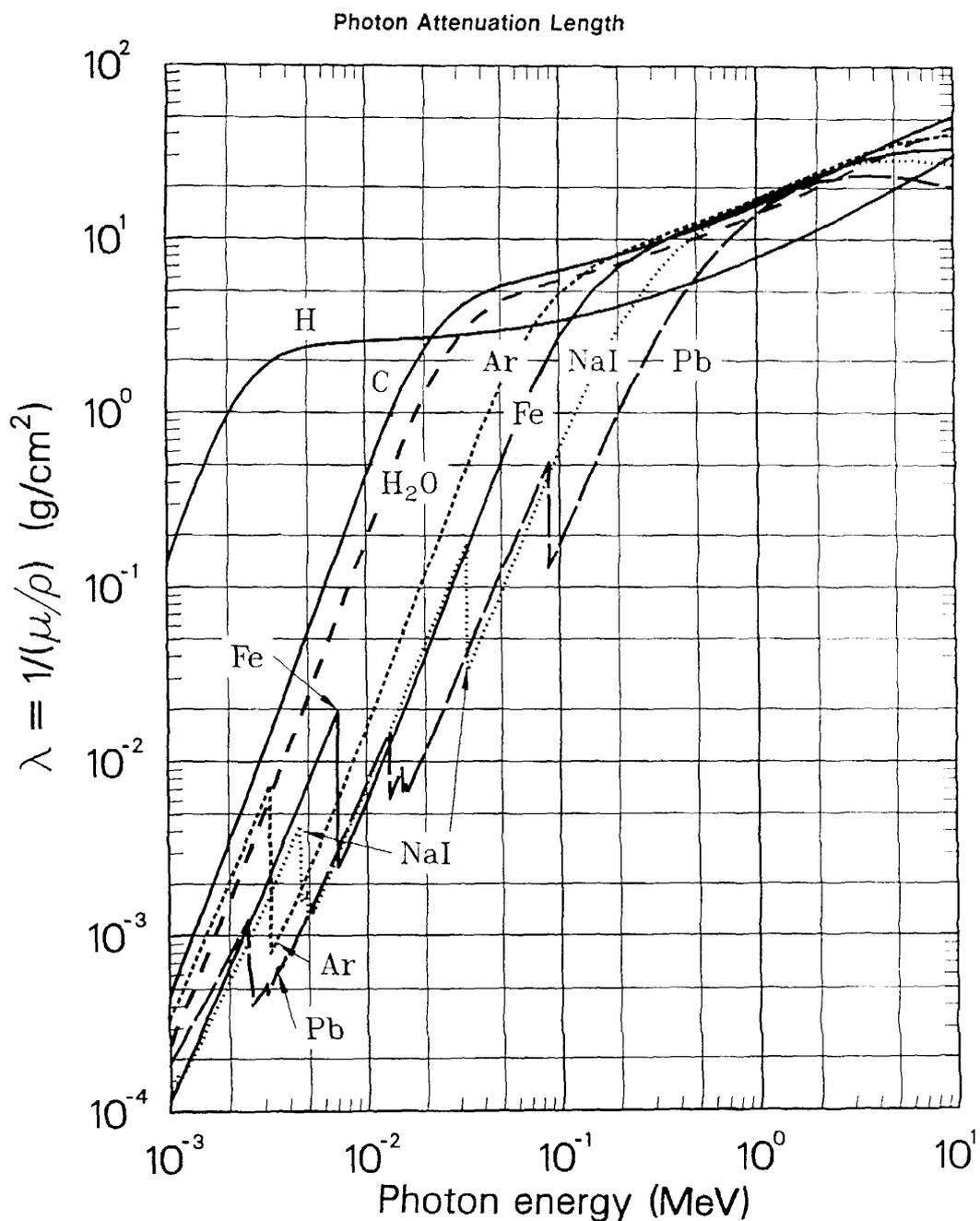
$$\frac{dW}{d\omega} = 0.52 \cdot \frac{e^2}{4\pi\epsilon_0 R} \cdot \left(\frac{\omega R}{c}\right)^{1/3} \quad [\text{Joule}] \quad [\text{A1}]$$

and for  $\omega \gg \omega_c$ : (note that there is no dependence on the energy of the beam!)

$$\frac{dW}{d\omega} = 2.17 \cdot \frac{e^2}{4\pi\epsilon_0} \cdot \frac{\gamma}{c} \cdot \sqrt{\frac{\omega}{\omega_c}} \cdot e^{-\frac{\omega}{\omega_c}} \quad [\text{Joule}] \quad [\text{A2}]$$

and for the total radiated Power:

$$W = \frac{1}{4\pi\epsilon_0} \cdot \frac{2}{3} \cdot \frac{c e^2 \gamma^4}{R^2} \quad [\text{Watt}] \quad [\text{A3}]$$



The photon mass attenuation length  $\lambda = 1/(\mu/\rho)$  (also known as mfp, mean free path) for various absorbers as a function of photon energy, where  $\mu$  is the mass attenuation coefficient. For a homogeneous medium of density  $\rho$ , the intensity  $I$  remaining after traversal of thickness  $t$  is given by the expression  $I = I_0 \exp(-t\rho/\lambda)$ . The accuracy is a few percent. Interpolation to other  $Z$  should be done in the cross section  $\sigma = A/\lambda N_A$  cm<sup>2</sup>/atom, where  $A$  is the atomic weight of the absorber material in grams and  $N_A$  is the Avogadro number. For a chemical compound or mixture, use  $(1/\lambda)_{\text{eff}} \cong \sum w_i (1/\lambda)_i$ , accurate to a few percent, where  $w_i$  is the proportion by weight of the  $i^{\text{th}}$  constituent. See next page for high energy range. The processes responsible for attenuation are given in the bottom figures of the next page. Not all of these processes necessarily result in detectable attenuation. For example, coherent Rayleigh scattering off an atom may occur at such low momentum transfer that the change in energy and momentum of the photon may not be significant. From Hubbell, Gimm, and Overbø, J. Phys. Chem. Ref. Data 9, 1023 (1980). See also J.H. Hubbell, Int. J. of Applied Rad. and Isotopes 33, 1269 (1982). Data courtesy J.H. Hubbell.

Fig. A2: Photon attenuation length for different materials, from Rev. Particle Properties, Phys. Letters B, Vol. 204, 1988

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Ref. 2: J.D. Jackson; **Klassische Elektrodynamik**  
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Ref. 3: J.A.R. Samson; **Techniques of Vacuum-Ultraviolet Spectroscopy**, John Wiley & Sons, Inc. New York

Ref. 4: M. Seebach, M. Werner; DESY MKI, privat communication, and **Photon beam position monitors at DORIS, DIPAC**, Frascati

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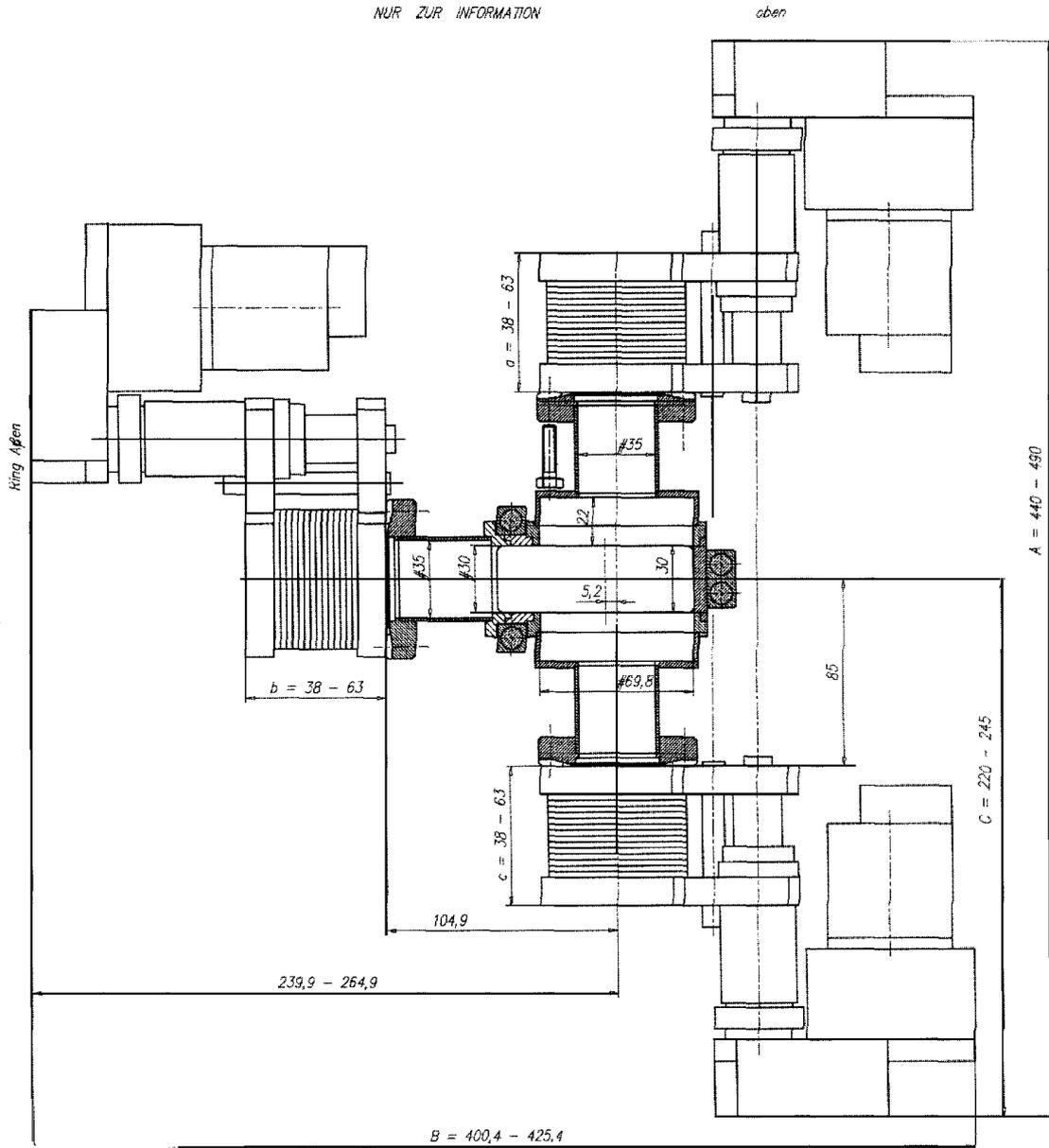
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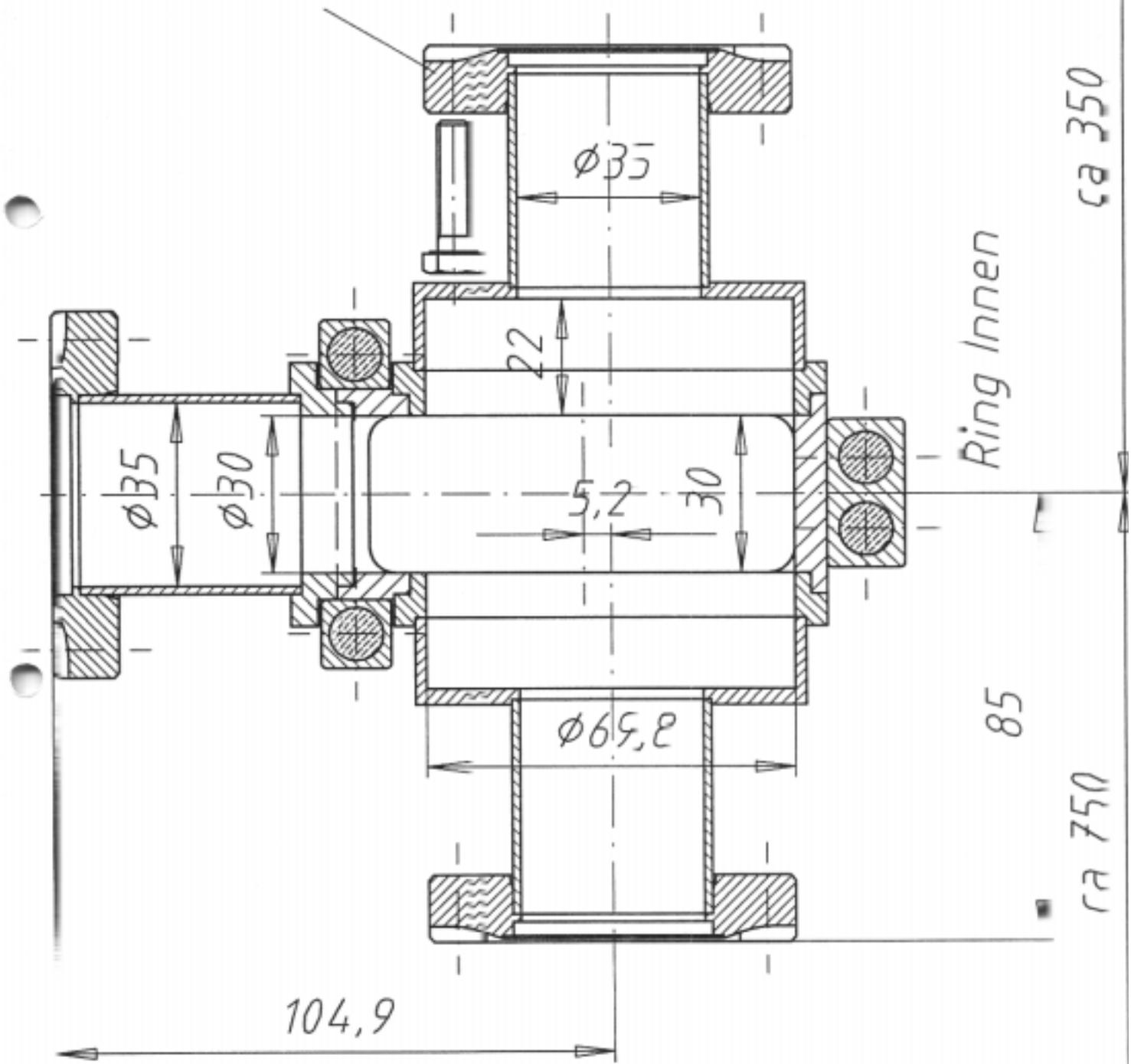
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